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(71) Applicant *(for all designated States except US)*: **LAM RESEARCH CORPORATION** [US/US]; 4650 Cushing Parkway, Fremont, CA 94538 (US).

(72) Inventors; and

(75) Inventors/Applicants *(for US only)*: **SIRARD, Stephen, M.** [US/US]; 7136 Chimney Cors, Austin, TX 78731 (US). **TAKESHITA, Kenji** [JP/US]; 1471 Yukon Drive, Sunnyvale, CA 94087 (US). **BAILEY III, Andrew D.** [US/US]; 3363 Sagewood Court, Pleasanton, CA 94588 (US).

(74) Agents: **LEE, Michael B.K.** et al.; Beyer Law Group LLP, P.O. Box 1687, Cupertino, CA 95015-1687 (US).

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(54) Title: METHOD FOR REPAIRING LOW-K DIELECTRIC DAMAGE

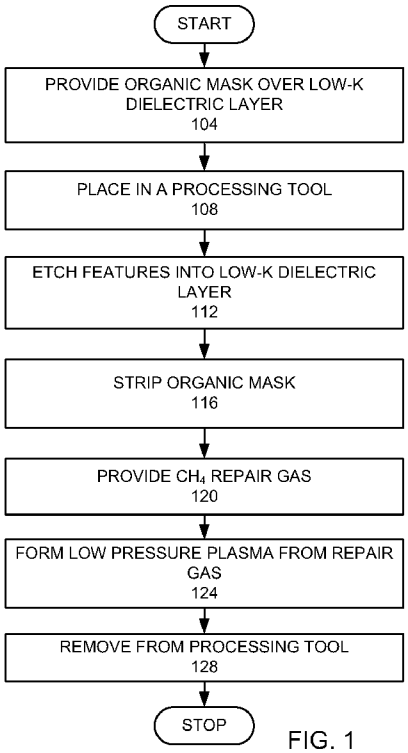


FIG. 1

(57) Abstract: A method for repairing damage to a silicon based low-k dielectric layer with organic compounds, where damage replaces a methyl attached to silicon with a hydroxyl attached to silicon is provided. A repair gas comprising CH_4 gas is provided. The repair gas is formed into a plasma, while maintaining a pressure below 50 mTorr. Hydroxyl attached to silicon is replaced with methyl from the plasma formed by the repair gas.

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